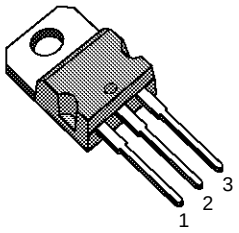
SGS-THOMSON MICROELECTRONICS

BUL58D

HIGH VOLTAGE FAST-SWITCHING NPN POWER TRANSISTOR

PRELIMINARY DATA

- HIGH VOLTAGE CAPABILITY
- LOW SPREAD OF DYNAMIC PARAMETERS
- MINIMUM LOT-TO-LOT SPREAD FOR RELIABLE OPERATION
- LOW BASE-DRIVE REQUIREMENTS
- VERY HIGH SWITCHING SPEED
- FULLY CHARACTERISED AT 125°C
- HIGH RUGGEDNESS
- INTEGRATED ANTIPARALLEL COLLECTOR-EMITTER DIODE



TO-220

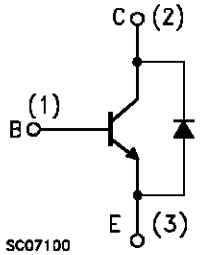
APPLICATIONS

- ELECTRONIC TRANSFORMERS FOR HALOGEN LAMPS
- ELECTRONIC BALLASTS FOR FLUORESCENT LIGHTING
- SWITCH MODE POWER SUPPLIES

DESCRIPTION

The BUL58D is manufactured using high voltage Multi Epitaxial Planar technology to enhance switching speeds while maintaining a wide RBSOA.
The BUL series is designed for use in lighting applications and low cost switch-mode power supplies.

INTERNAL SCHEMATIC DIAGRAM



ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V_{CES}	Collector-Emitter Voltage (V_{BE} = 0)	800	V
V_{CEO}	Collector-Emitter Voltage (I_B = 0)	450	V
V_{EBO}	Emitter-Base Voltage (I_C = 0)	10	V
I_C	Collector Current	8	A
I_{CM}	Collector Peak Current (t_p < 5 ms)	12	A
I_B	Base Current	4	A
I_{BM}	Base Peak Current (t_p < 5 ms)	8	A
P_{tot}	Total Dissipation at T_c = 25 °C	75	W
T_{stg}	Storage Temperature Range	-65 to 150	°C
T_j	Max. Operating Junction Temperature	150	°C

THERMAL DATA

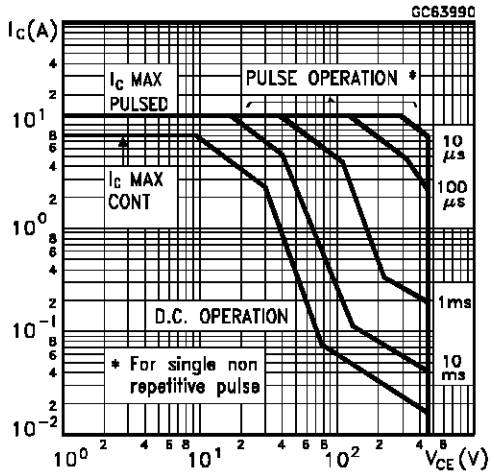
$R_{thj\text{-}case}$	Thermal Resistance Junction-Case	Max	1.65	°C/W
$R_{thj\text{-}amb}$	Thermal Resistance Junction-Ambient	Max	62.5	°C/W

ELECTRICAL CHARACTERISTICS (T_{case} = 25 °C unless otherwise specified)

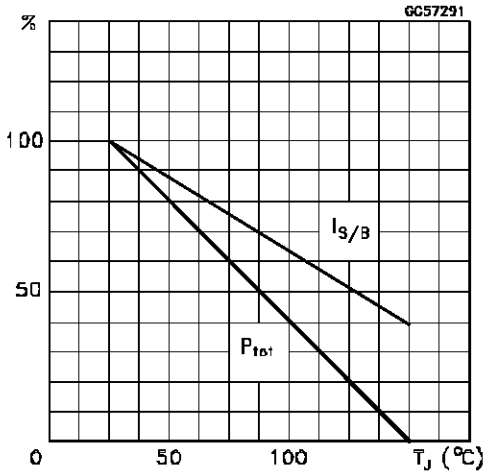
Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
I_{CES}	Collector Cut-off Current (V_{BE} = 0)	V_{CE} = 800 V			200	µA
I_{CEO}	Collector Cut-off Current (I_B = 0)	V_{CE} = 450 V			200	µA
$V_{CEO(sus)}$	Collector-Emitter Sustaining Voltage	I_C = 100 mA L = 25 mH	450			V
V_{EBO}	Emitter-Base Voltage (I_C = 0)	I_E = 10 mA	9			V
$V_{CE(sat)}$*	Collector-Emitter Saturation Voltage	I_C = 4 A I_B = 0.8 A I_C = 5 A I_B = 1 A			1.5 2	V V
$V_{BE(sat)}$*	Base-Emitter Saturation Voltage	I_C = 4 A I_B = 0.8 A I_C = 5 A I_B = 1 A			1.3 1.5	V V
h_{FE}*	DC Current Gain	I_C = 5 A V_{CE} = 5 V I_C = 500 mA V_{CE} = 5 V	5	 38		
 t_s t_f	INDUCTIVE LOAD Storage Time Fall Time	I_C = 2 A I_{B1} = 0.4 A $V_{BE(off)}$ = -5 V R_{BB} = 0 Ω V_{CL} = 250 V L = 200 µH		 1 90	 1.8 180	 µs ns
 t_s t_f	INDUCTIVE LOAD Storage Time Fall Time	I_C = 2 A I_{B1} = 0.4 A $V_{BE(off)}$ = -5 V R_{BB} = 0 Ω V_{CL} = 250 V L = 200 µH T_j = 125 °C		 1.5 180		 µs ns
V_f	Diode Forward Voltage	I_C = 3 A			3	V

∗ Pulsed: Pulse duration = 300 µs, duty cycle 1.5 %

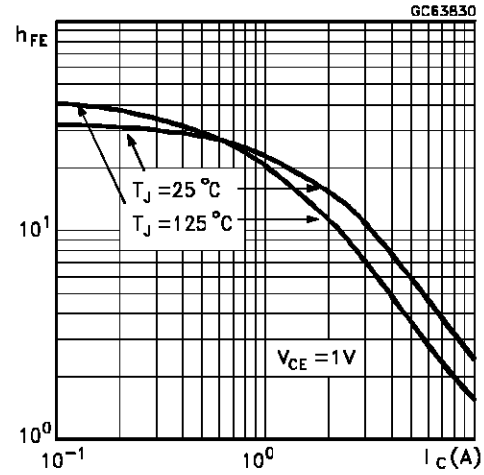
Safe Operating Areas



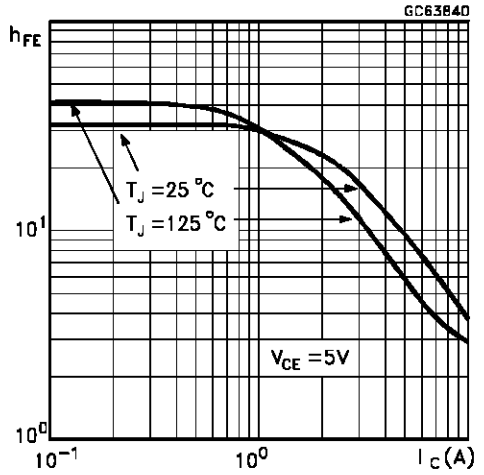
Derating Curves



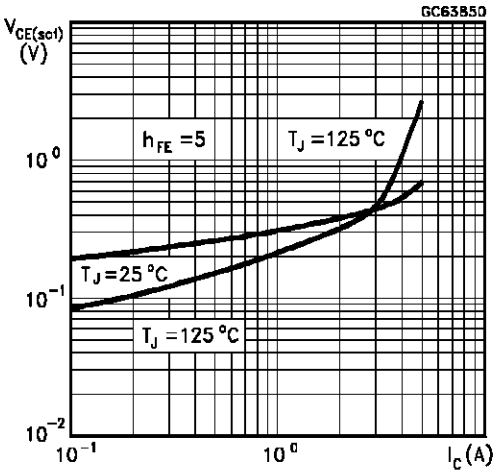
DC Current Gain



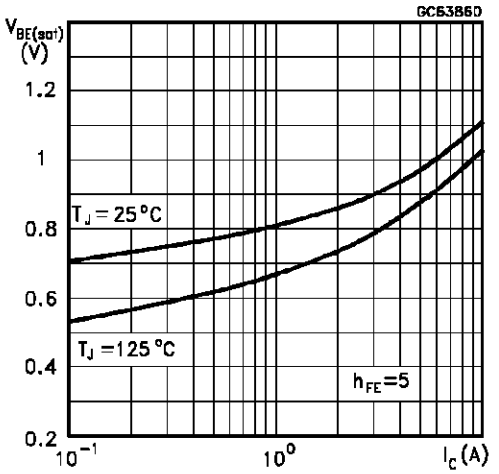
DC Current Gain



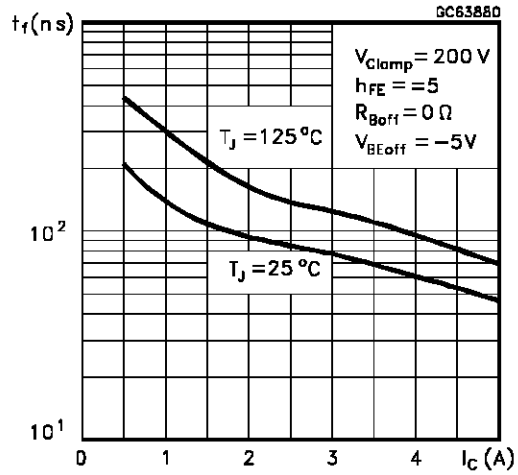
Collector Emitter Saturation Voltage



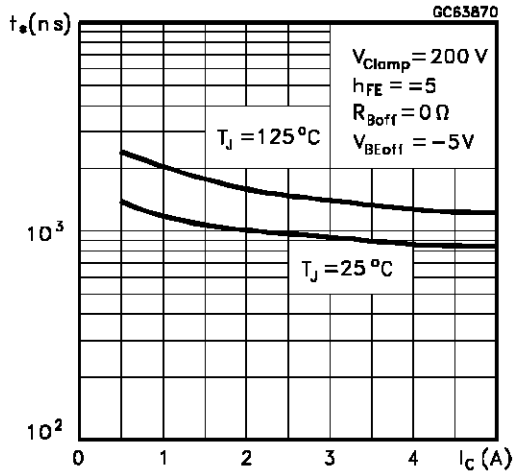
Base Emitter Saturation Voltage



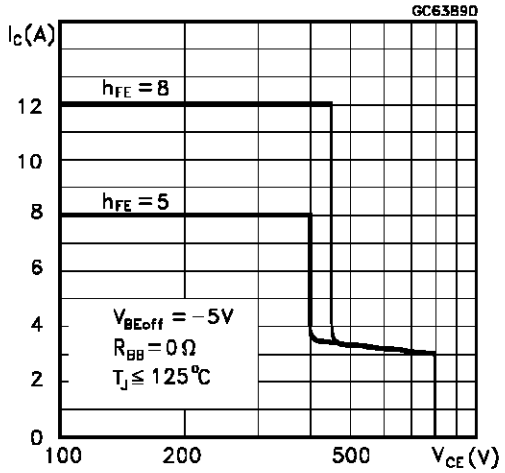
Inductive Fall Time



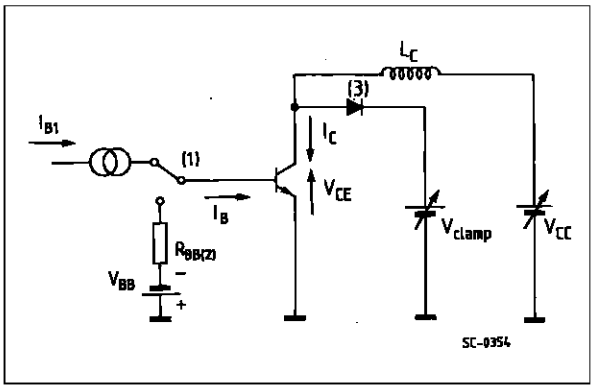
Inductive Storage Time



Reverse Biased SOA



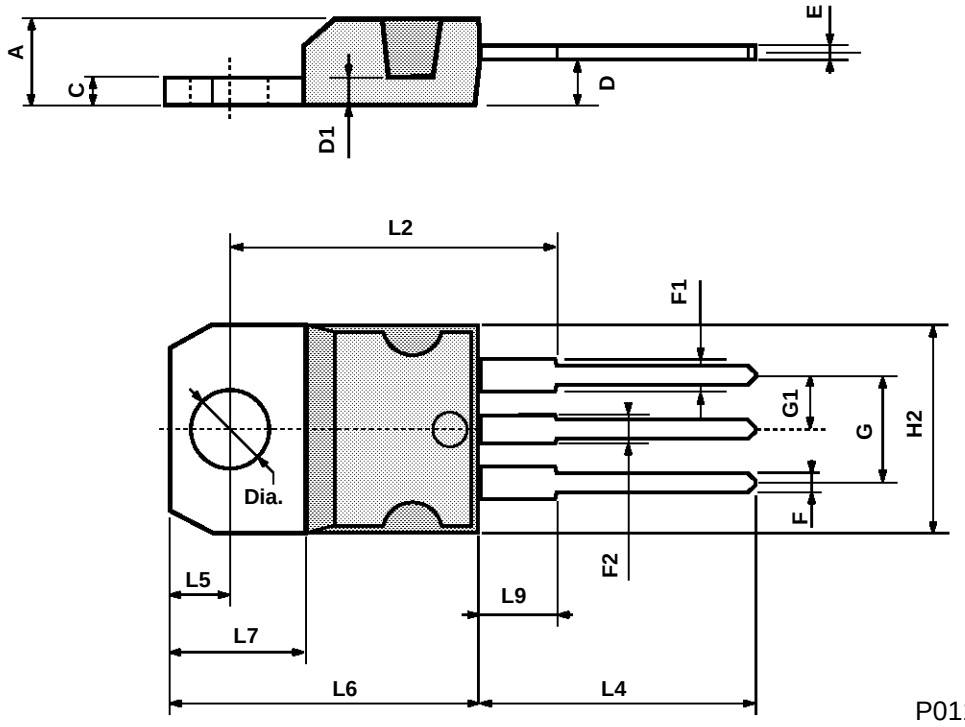
RBSOA and Inductive Load Switching Test Circuit



(1) Fast electronic switch
(2) Non-inductive Resistor
(3) Fast recovery rectifier

TO-220 MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	4.40		4.60	0.173		0.181
C	1.23		1.32	0.048		0.051
D	2.40		2.72	0.094		0.107
D1		1.27			0.050	
E	0.49		0.70	0.019		0.027
F	0.61		0.88	0.024		0.034
F1	1.14		1.70	0.044		0.067
F2	1.14		1.70	0.044		0.067
G	4.95		5.15	0.194		0.203
G1	2.4		2.7	0.094		0.106
H2	10.0		10.40	0.393		0.409
L2		16.4			0.645	
L4	13.0		14.0	0.511		0.551
L5	2.65		2.95	0.104		0.116
L6	15.25		15.75	0.600		0.620
L7	6.2		6.6	0.244		0.260
L9	3.5		3.93	0.137		0.154
DIA.	3.75		3.85	0.147		0.151



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